

ABSTRACT OF THE DISCLOSURE

A method for manufacturing a miniaturized semiconductor device having a conductive portion with a silicide structure. The manufacturing method includes depositing metal on the surface of a patterned semiconductor film to form the conductive portion, heat treating the semiconductor film on which the metal is deposited, removing the residual metal that did not react during the heat treatment, and repeating the depositing step, the heat treating step, and the removing step once or a number of times.